Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM7®
Core Size	32-Bit Single-Core
Speed	66MHz
Connectivity	HDLC, I²C, SmartCard, SPI, UART/USART, USB
Peripherals	PWM, WDT
Number of I/O	30
Program Memory Size	128KB (128K x 8 + 16K)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 3.6V
Data Converters	A/D 4x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/str711fr1t6

Contents

List of figures

1 Introduction

This datasheet provides the STR71x pinout, ordering information, mechanical and electrical device characteristics.

For complete information on the STR71x microcontroller memory, registers and peripherals. please refer to the STR71x reference manual.

For information on programming, erasing and protection of the internal Flash memory please refer to the STR7 Flash programming reference manual.

For information on the ARM7TDMI core please refer to the ARM7TDMI technical reference manual.

Table 2. Device overview

Features	STR710 FZ1	STR710 FZ2	STR710 RZ	STR711 FR0	STR711 FR1	STR711 FR2	STR712 FR0	STR712 FR1	STR712 FR2	STR715 FRx
Flash - Kbytes	128+16	256+16	0	64+16	128+16	256+16	64+16	128+16	256+16	64+16
RAM - Kbytes	32	64	64	16	32	64	16	32	64	16
Peripheral Functions	CAN, EMI, USB, 48 I/Os			USB, 30 I/Os			CAN, 32 I/Os			32 I/Os
Operating Voltage	3.0 to 3.6 V									
Operating Temperature	-40 to +85°C or 0 to 70° C									
Packages	**T**=LQFP144 20 x 20 **H**=LFBGA144 10 x10			**T**=LQFP64 10 x10						

.

3 System architecture

Package choice: low pin-count 64-pin or feature-rich 144-pin LQFP or BGA

The STR71x family is available in 5 main versions.

The 144-pin versions have the full set of all features including CAN, USB and External Memory Interface (EMI).

- **STR710F:** 144-pin BGA or LQFP with CAN, USB and EMI
- **STR710R:** Flashless 144-pin BGA or LQFP with CAN, USB and EMI (no internal Flash memory)

The three 64-pin versions (LQFP) do not include External Memory Interface.

- **STR715F:** 64-pin LQFP without CAN or USB
- **STR711F:** 64-pin LQFP with USB
- **STR712F:** 64-pin LQFP with CAN

High speed Flash memory (STR71xF)

The Flash program memory is organized in two banks of 32-bit wide Burst Flash memories enabling true read-while-write (RWW) operation. Device Bank 0 is up to 256 Kbytes in size, typically for the application program code. Bank 1 is 16 Kbytes, typically used for storing data constants. Both banks are accessed by the CPU with zero wait states @ 33 MHz

Bank 0 memory endurance is 10K write/erase cycles and Bank 1 endurance is 100K write/erase cycles. Data retention is 20 years at 85°C on both banks. The two banks can be accessed independently in read or write. Flash memory can be accessed in two modes:

- Burst mode: 64-bit wide memory access at up to 50 MHz.
- Direct 32-bit wide memory access for deterministic operation at up to 33 MHz.

The STR7 embedded Flash memory can be programmed using In-Circuit Programming or In-Application programming.

IAP (in-application programming): The IAP is the ability to re-program the Flash memory of a microcontroller while the user program is running.

ICP (in-circuit programming): The ICP is the ability to program the Flash memory of a microcontroller using JTAG protocol while the device is mounted on the user application board.

The Flash memory can be protected against different types of unwanted access (read/write/erase). There are two types of protection:

- Sector Write Protection
- Flash Debug Protection (locks JTAG access)

Refer to the STR7 Flash Programming Reference manual for details.

Optional external memory (STR710)

The non-multiplexed 16-bit data/24-bit address bus available on the STR710 (144-pin) supports four 16-Mbyte banks of external memory. Wait states are programmable individually for each bank allowing different memory types (Flash, EPROM, ROM, SRAM etc.) to be used to store programs or data.

Figure 1 shows the general block diagram of the device family.

3.3 Pin description for 144-pin packages

Figure 2. STR710 LQFP pinout

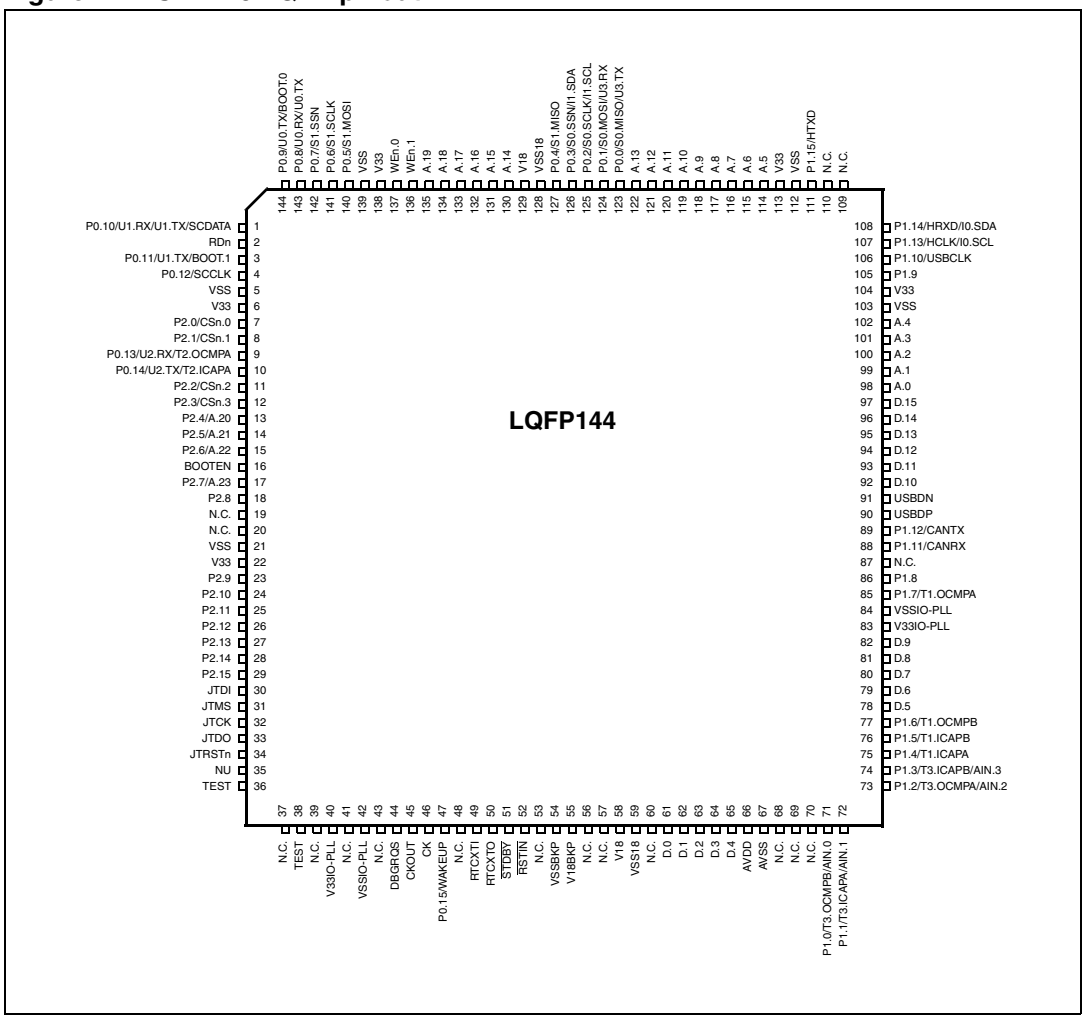


Table 4. STR710 pin description

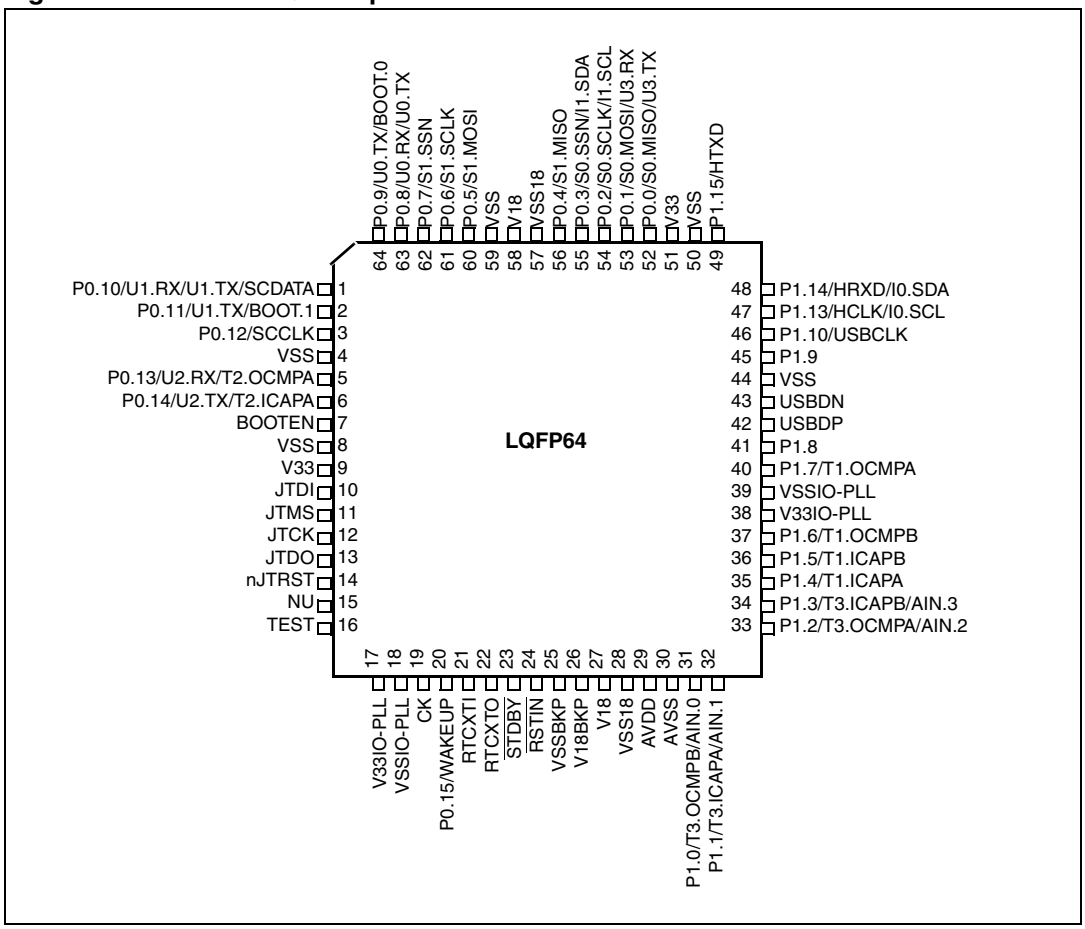
Pin n°		Pin name	Type	Reset state[1]	Input		Output			Active in Stdby	Main function (after reset)	Alternate function
LQFP144	BGA144				Input level	interrupt	Capability	OD	PP			
40	K3	$V_{33IO-PLL}$	S								Supply voltage for digital I/O circuitry and for PLL reference	
41	M4	N.C.									Not connected (not bonded)	
42	L4	$V_{SSIO-PLL}$	S								Ground voltage for digital I/O circuitry and for PLL reference[4]	
43	M2	N.C.									Not connected (not bonded)	
44	M3	DBGRQS	I		C_T						Debug Mode request input (active high)	
45	K4	CKOUT	O				8mA		X		Clock output (f_{PCLK2}) **Note:** Enabled by CKDIS register in APB Bridge 2	
46	J4	CK	I		C						Reference clock input	
47	M5	P0.15/ WAKEUP	I		T_T	X				X	Port 0.15	Wakeup from Standby mode input. **Note:** This port is input only.
48	L5	N.C.									Not connected (not bonded)	
49	K5	RTCXTI									Realtime Clock input and input of 32 kHz oscillator amplifier circuit	
50	J5	RTCXTO									Output of 32 kHz oscillator amplifier circuit	
51	M6	$\overline{STDBY}$	I/O		C_T		4mA	X		X	Input: Hardware Standby mode entry input active low. **Caution:** External pull-up to V_{33} required to select normal mode. Output: Standby mode active low output following Software Standby mode entry. **Note**: In Standby mode all pins are in high impedance except those marked Active in Stdby	
52	M7	$\overline{RSTIN}$	I		C_T					X	Reset input	
53	H5	N.C.									Not connected (not bonded)	
54	L6	V_{SSBKP}			S					X	Stabilization for low power voltage regulator.	
55	K6	V_{18BKP}			S					X	Stabilization for low power voltage regulator. Requires external capacitors of at least 1µF between V_{18BKP} and $V_{SS18BKP}$. See *Figure 5*. **Note:** If the low power voltage regulator is bypassed, this pin can be connected to an external 1.8V supply.	
56	J6	N.C.									Not connected (not bonded)	
57	H6	N.C.									Not connected (not bonded)	
58	G6	V_{18}	S								Stabilization for main voltage regulator. Requires external capacitors of at least 10µF + 33nF between V_{18} and V_{SS18}. See *Figure 5*.	

Table 4. STR710 pin description

Pin n°		Pin name	Type	Reset state[1]	Input		Output			Active in Stdby	Main function (after reset)	Alternate function	
LQFP144	BGA144				Input level	interrupt	Capability	OD	PP				
143	C4	P0.8/U0.RX/ U0.TX	I/O	pd	C_T	X	4mA	T			Port 0.8	UART0: Receive Data input	UART0: Transmit data output.
											Note: This pin may be used for single wire UART (half duplex) if programmed as Alternate Function Output. The pin will be tri-stated except when UART transmission is in progress		
144	B3	P0.9/U0.TX/ BOOT.0	I/O	pd	C_T		4mA	X	X		Port 0.9	Select Boot Configuration input	UART0: Transmit data output

1. The Reset configuration of the I/O Ports is IPUPD (input pull-up/pull down). Refer to *Table 6 on page 30*. The Port bit configuration at reset is PC0=1, PC1=1, PC2=0. The port data register bit (PD) value depends on the pu/pd column which specifies whether the pull-up or pull-down is enabled at reset
2. In reset state, these pins configured as Input PU/PD with weak pull-up enabled. They must be configured by software as Alternate Function (see *Table 6: Port bit configuration table on page 30*) to be used by the External Memory Interface.
3. In reset state, these pins configured as Input PU/PD with weak pull-down enabled to output Address 0x0000 0000 using the External Memory Interface. To access memory banks greater than 1Mbyte, they need to be configured by software as Alternate Function (see *Table 6: Port bit configuration table on page 30*).
4. $V_{33IO\text{-}PLL}$ and V_{33} are internally connected. $V_{SSIO\text{-}PLL}$ and V_{SS} are internally connected.
5. During the reset phase, these pins are in input pull-up state. When reset is released, they are configured as Output Push-Pull.
6. During the reset phase, these pins are in input pull-up state. When reset is released, they are configured as Hi-Z.
7. During the reset phase, these pins are in input pull-down state. When reset is released, they are configured as Output Push-Pull.
8. During the reset phase, this pin is in input floating state. When reset is released, it is configured as Output Push-Pull.

Figure 4. STR711 LQFP64 pinout



Legend / abbreviations for *Table 5*:

Type: I = input, O = output, S = supply, HiZ= high impedance,

In/Output level: C = CMOS $0.3V_{DD}/0.7V_{DD}$
C_T= CMOS $0.3V_{DD}/0.7V_{DD}$ with input trigger
T_T= TTL 0.8V / 2V with input trigger
C/T = Programmable levels: CMOS $0.3V_{DD}/0.7V_{DD}$ or TTL 0.8V / 2V

Port and control configuration:

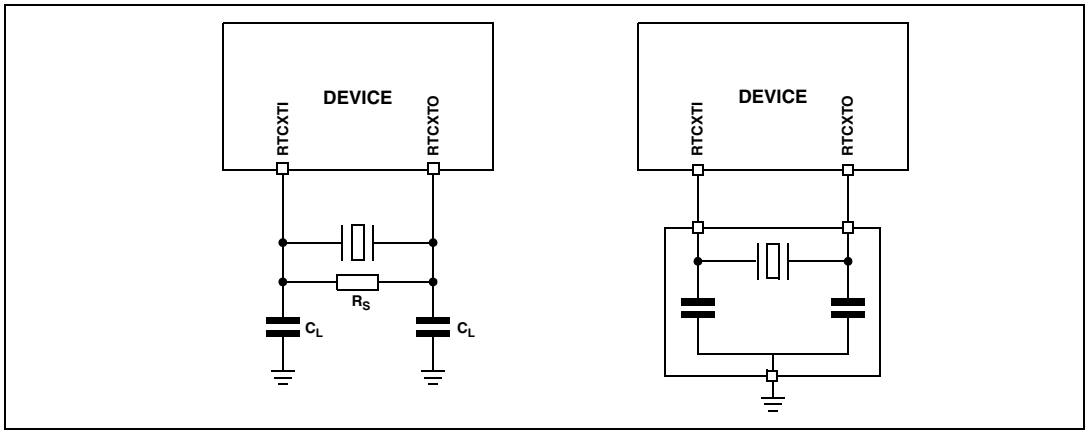
Input: pu/pd= software enabled internal pull-up or pull down
pu= in reset state, the internal 100kΩ weak pull-up is enabled.
pd = in reset state, the internal 100kΩ weak pull-down is enabled.

Output: OD = open drain (logic level)
PP = push-pull
T = true OD, (P-Buffer and protection diode to V_{DD} not implemented), 5V tolerant.

Table 5. STR711/STR712/STR715 pin description (continued)

Pin n°	Pin name	Type	Reset state[1)]	Input		Output			Active in Stdby	Main function (after reset)	Alternate function	
LQFP64				Input level	interrupt	Capability	OD	PP				
52	P0.0/S0.MISO /U3.TX	I/O	pu	C_T		4mA	X	X		Port 0.0	SPI0 Master in/Slave out data	UART3 Transmit data output
											Note: Programming AF function selects UART by default. BSPI must be enabled by SPI_EN bit in the BOOTCR register.	
53	P0.1/S0.MOSI /U3.RX	I/O	pu	C_T	X	4mA	X	X		Port 0.1	BSPI0: Master out/Slave in data	UART3: Receive Data input
											Note: Programming AF function selects UART by default. BSPI must be enabled by SPI_EN bit in the BOOTCR register.	
54	P0.2/S0.SCLK /I1.SCL	I/O	pu	C_T	X	4mA	X	X		Port 0.2	BSPI0: Serial Clock	I2C1: Serial clock
											Note: Programming AF function selects I2C by default. BSPI must be enabled by SPI_EN bit in the BOOTCR register.	
55	P0.3/S0.$\overline{SS}$/I1 .SDA	I/O	pu	C_T		4mA	X	X		Port 0.3	SPI0: Slave Select input active low.	I2C1: Serial Data
											Note: Programming AF function selects I2C by default. BSPI must be enabled by SPI_EN bit in the BOOTCR register.	
56	P0.4/S1.MISO	I/O	pu	C_T		4mA	X	X		Port 0.4	SPI1: Master in/Slave out data	
57	V_{SS18}	S								Stabilization for main voltage regulator.		
58	V_{18}	S								Stabilization for main voltage regulator. Requires external capacitors of at least 10µF + 33nF between V_{18} and V_{SS18}. See *Figure 5*.		
59	V_{SS}	S								Ground voltage for digital I/Os		
60	P0.5/S1.MOSI	I/O	pu	C_T		4mA	X	X		Port 0.5	SPI1: Master out/Slave In data	
61	P0.6/S1.SCLK	I/O	pu	C_T	X	4mA	X	X		Port 0.6	SPI1: Serial Clock	
62	P0.7/S1.$\overline{SS}$	I/O	pu	C_T		4mA	X	X		Port 0.7	SPI1: Slave Select input active low	

Figure 16. RTC crystal oscillator and resonator



PLL electrical characteristics

V_{33} = 3.0 to 3.6V, $V_{33IOPLL}$ = 3.0 to 3.6V, T_A = -40 / 85 °C unless otherwise specified.

Table 19. PLL1 characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min	Typ	Max	
$f_{PLLCLK1}$	PLL multiplier output clock				165	MHz
f_{PLL1}	PLL input clock	FREF_RANGE = 0	1.5		3.0	MHz
		FREF_RANGE = 1 MX[1:0]='00' or '01'	3.0		8.25	MHz
		FREF_RANGE = 1 MX[1:0]='10' or '11'	3.0		6	MHz
	PLL input clock duty cycle		25		75	%
f_{FREE1}	PLL free running frequency	FREF_RANGE = 0 MX[1:0]='01' or '11'		125		kHz
		FREF_RANGE = 0 MX[1:0]='00' or '10'		250		kHz
		FREF_RANGE = 1 MX[1:0]='01' or '11'		250		kHz
		FREF_RANGE = 1 MX[1:0]='00' or '10'		500		kHz
t_{LOCK1}	PLL lock time	FREF_RANGE = 0 Stable Input Clock Stable $V_{33IOPLL}$, V_{18}			300	µs
		FREF_RANGE = 1 Stable Input Clock Stable $V_{33IOPLL}$, V_{18}			600	µs

Table 25. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Maximum value [1]	Unit
$V_{ESD(HBM)}$	Electro-static discharge voltage (Human Body Model)	T_A=+25°C	2000	V
$V_{ESD(MM)}$	Electro-static discharge voltage (Machine Model)		200	
$V_{ESD(CDM)}$	Electro-static discharge voltage (Charge Device Model)		750 on corner pins, 500 on others	

Notes:

1. Data based on characterization results, not tested in production.

Static and dynamic latch-up

- **LU**: 3 complementary static tests are required on 10 parts to assess the latch-up performance. A supply overvoltage (applied to each power supply pin) and a current injection (applied to each input, output and configurable I/O pin) are performed on each sample. This test conforms to the EIA/JESD 78 IC latch-up standard. For more details, refer to the application note AN1181.
- **DLU**: Electro-Static Discharges (one positive then one negative test) are applied to each pin of 3 samples when the micro is running to assess the latch-up performance in dynamic mode. Power supplies are set to the typical values, the oscillator is connected as near as possible to the pins of the micro and the component is put in reset mode. This test conforms to the IEC1000-4-2 and SAEJ1752/3 standards. For more details, refer to the application note AN1181.

Electrical sensitivities

Table 26. Static and dynamic latch-up

Symbol	Parameter	Conditions	Class[1]
LU	Static latch-up class	T_A=+25°C T_A=+85°C T_A=+105°C	A A A
DLU	Dynamic latch-up class	V_{DD}=3.3 V, f_{OSC4M}=4 MHz, f_{MCLK}=32 MHz, T_A=+25°C	A

1. Class description: A Class is an STMicroelectronics internal specification. All its limits are higher than the JEDEC specifications, that means when a device belongs to Class A it exceeds the JEDEC standard. B Class strictly covers all the JEDEC criteria (international standard).

4.3.5 I/O port pin characteristics

General characteristics

Subject to general operating conditions for V_{33} and T_A unless otherwise specified. All unused pins must be kept at a fixed voltage: using the output mode of the I/O for example or an external pull-up or pull-down resistor.

Table 27. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage 1)	CMOS ports			$0.3V_{33}$	V
V_{IH}	Input high level voltage 1)		$0.7V_{33}$			
V_{hys}	Schmitt trigger voltage hysteresis 2)			0.8		V
V_{IL}	Input low level voltage 1)	P0.15 WAKEUP		0.9	0.8	V
V_{IH}	Input high level voltage 1)		2	1.35		
V_{hys}	Schmitt trigger voltage hysteresis 2)			0.4		V
V_{IL}	Input low level voltage 1)	TTL ports			0.8	V
V_{IH}	Input high level voltage 1)		2.0			
$I_{INJ(PIN)}$	Injected Current on any I/O pin				± 4	mA
$\Sigma I_{INJ(PIN)}$ 3)	Total injected current (sum of all I/O and control pins)				± 25	
I_{lkg}	Input leakage current 4)	$V_{SS} \le V_{IN} \le V_{33}$			±1	µA
R_{PU}	Weak pull-up equivalent resistor5)	$V_{IN}=V_{SS}$	110	150	700	kΩ
R_{PD}	Weak pull-down equivalent resistor5)	$V_{IN}=V_{33}$	110	150	700	kΩ
C_{IO}	I/O pin capacitance			5		pF

Notes:

1. Data based on characterization results, not tested in production.
2. Hysteresis voltage between Schmitt trigger switching levels. Based on characterization results, not tested.
3. When the current limitation is not possible, the V_{IN} absolute maximum rating must be respected, otherwise refer to $I_{INJ(PIN)}$ specification. A positive injection is induced by $V_{IN}>V_{33}$ while a negative injection is induced by $V_{IN}<V_{SS}$. Refer to *Section 4.2 on page 35* for more details.
4. Leakage could be higher than max. if negative current is injected on adjacent pins.
5. The R_{PU} pull-up and R_{PD} pull-down equivalent resistor are based on a resistive transistor (corresponding I_{PU} and I_{PD} current characteristics described in *Figure 18* to *Figure 19*).

Figure 17. R_{PU} vs. V_{33} with $V_{IN}=V_{SS}$

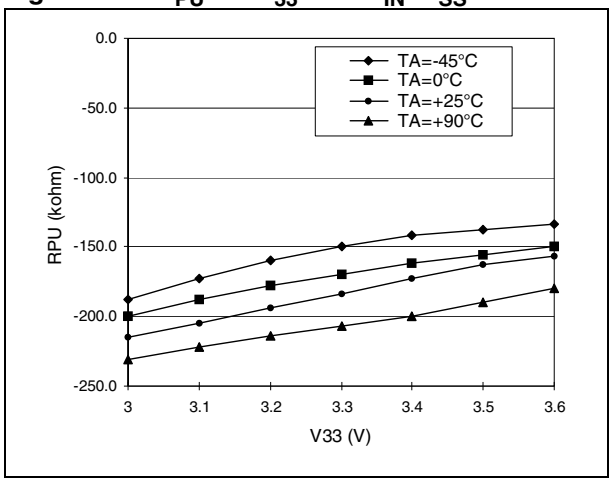


Figure 18. I_{PU} vs. V_{33} with $V_{IN}=V_{SS}$

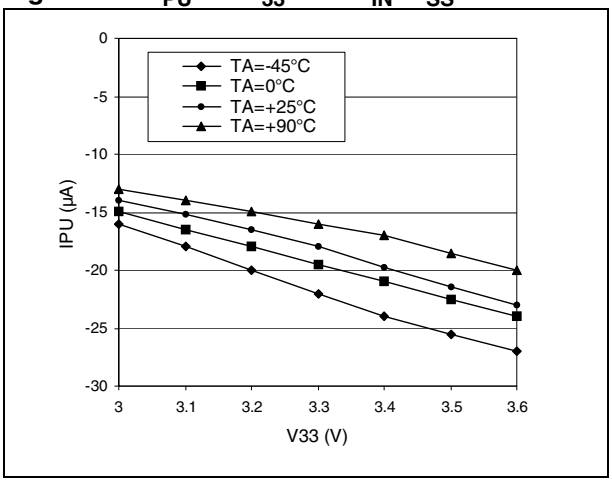


Figure 19. R_{PD} vs. V_{33} with $V_{IN}=V_{33}$

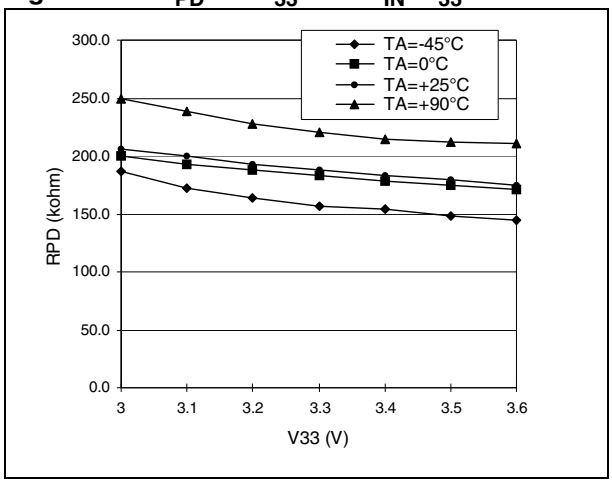


Figure 20. I_{PD} vs. V_{33} with $V_{IN}=V_{33}$

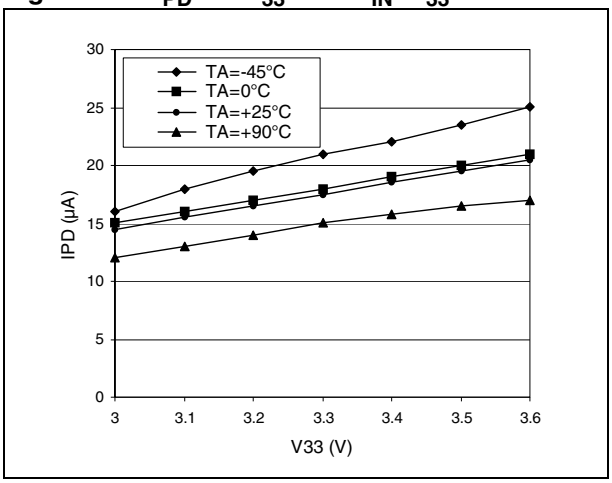


Figure 22. Typical V_{OL} vs. V_{33}

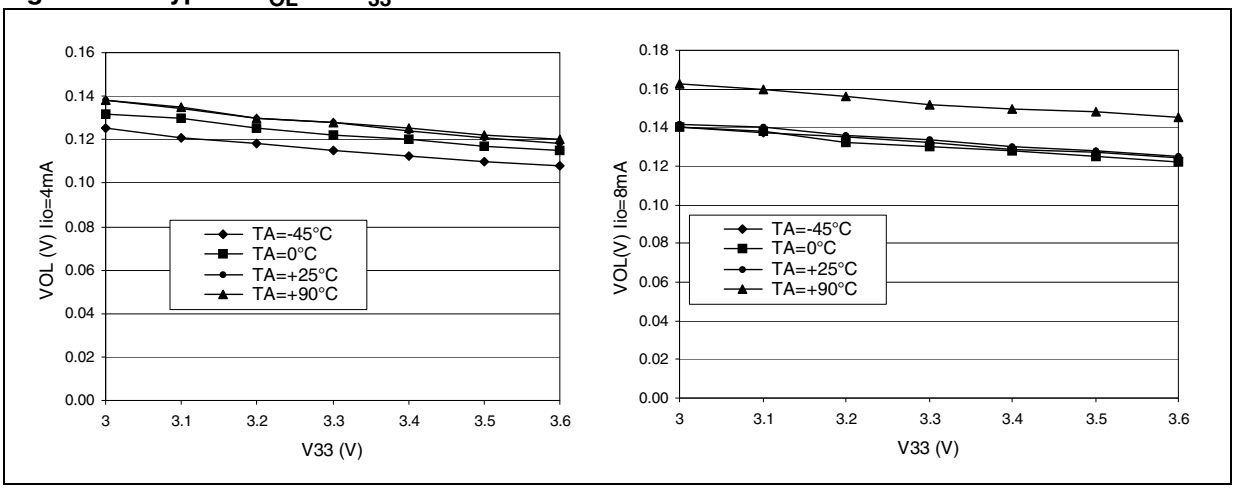


Figure 23. Typical V_{OH} vs. V_{33}

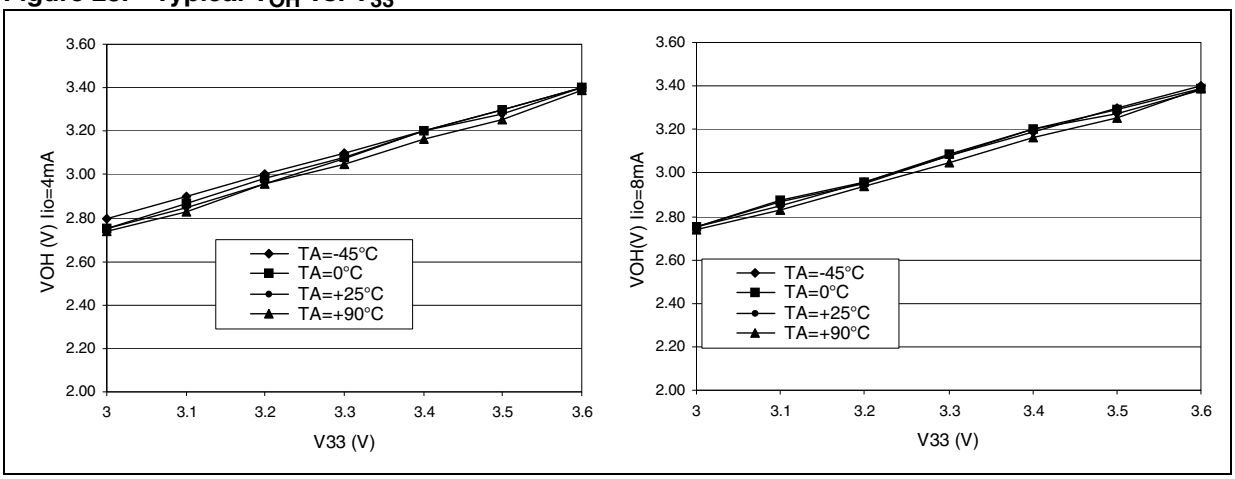


Figure 25. Read cycle timing: 16-bit read on 16-bit memory

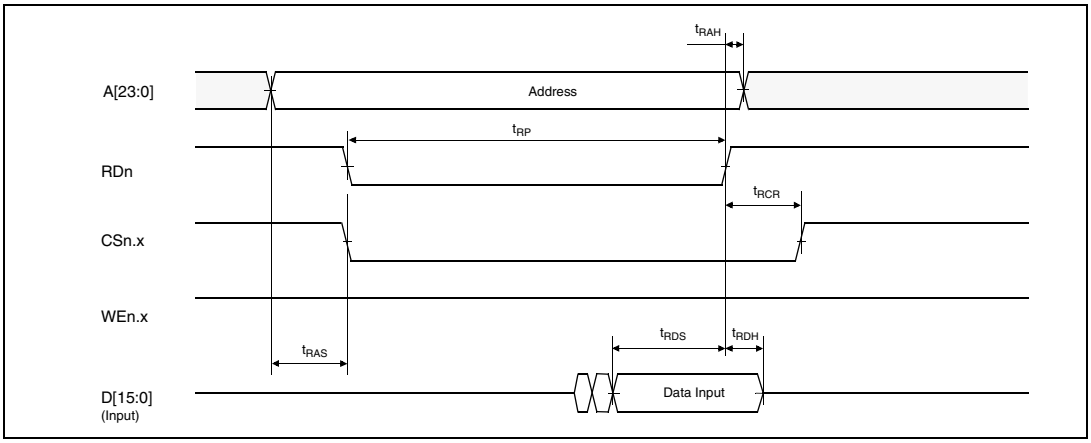
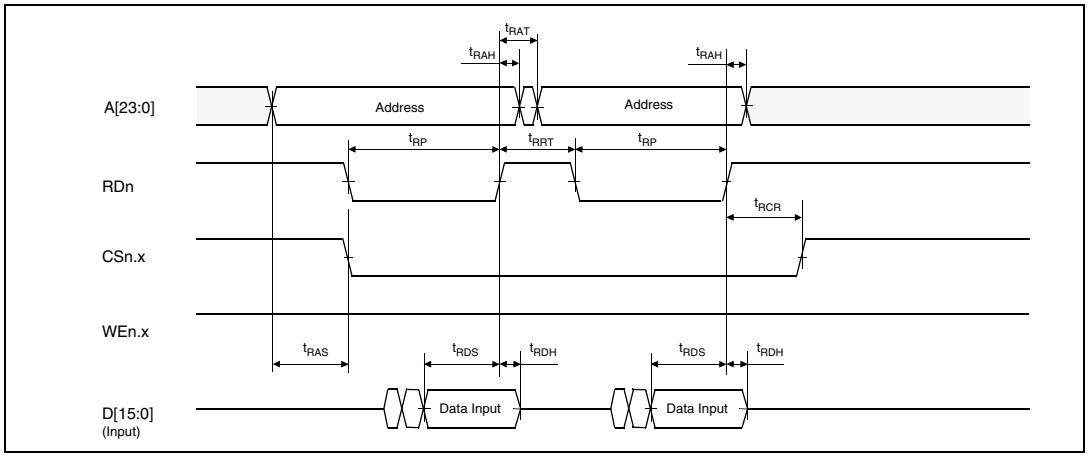
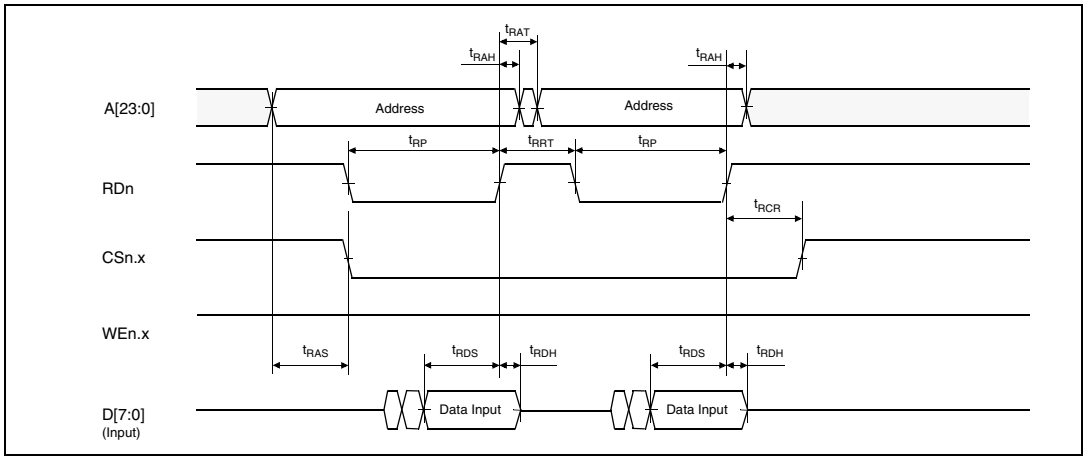


Figure 26. Read cycle timing: 32-bit read on 16-bit memory



See *Table 32* for read timing data.

Figure 27. Read cycle timing: 16-bit read on 8-bit memory



4.3.11 ADC characteristics

Subject to general operating conditions for AV_{DD}, f_{PCLK2}, and T_A unless otherwise specified.

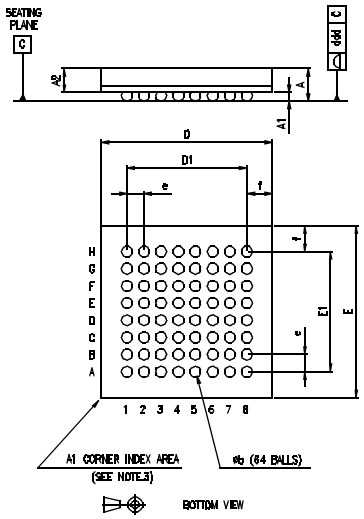
Table 40. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
f_{MOD}	Modulator Oversampling frequency				2.1	MHz
V_{AIN}	Conversion voltage range [2][3]		0		2.5	V
I_{lkg}	Negative input leakage current on analog pins	$V_{IN}<V_{SS}$, $\lvert I_{IN} \rvert <$ 400µA on adjacent analog pin		5	6	µA
PBR	Passband Ripple				0.1	dB
SINAD	S/N and Distortion		56	63		dB
THD	Total Harmonic Distortion		60	74		dB
Z_{IN}	Input Impedance	f_{MOD} = 2 MHz	1			MΩ
C_{ADC}	Internal sample and hold capacitor				3.2	pF
t_{CONV}	Total Conversion time (including sampling time)		2048/ f_{MOD} (max)			
I_{ADC}	Normal mode	T_A = 27 °C		2.5	3.0	mA
	Standby mode	T_A = 27 °C			1	µA

Notes:

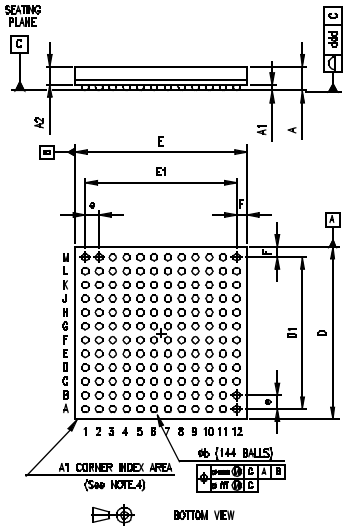
1. Unless otherwise specified, typical data are based on T_A=25°C and AV_{DD}-AV_{SS}=3.3V. They are given only as design guidelines and are not tested.
2. Any added external serial resistor will downgrade the ADC accuracy (especially for resistance greater than 10kΩ). Data based on characterization results, not tested in production.
3. Calibration is needed once after each power-up.

Figure 42. 64-Low profile fine pitch ball grid array package



Dim.	mm			inches		
	Min	Typ	Max	Min	Typ	Max
A	1.210		1.700	0.048		0.067
A1	0.270			0.011		
A2		1.120			0.044	
b	0.450	0.500	0.550	0.018	0.020	0.022
D	7.750	8.000	8.150	0.305	0.315	0.321
D1		5.600			0.220	
E	7.750	8.000	8.150	0.305	0.315	0.321
E1		5.600			0.220	
e	0.720	0.800	0.880	0.028	0.031	0.035
f	1.050	1.200	1.350	0.041	0.047	0.053
ddd			0.120			0.005
	Number of Pins					
N	64					

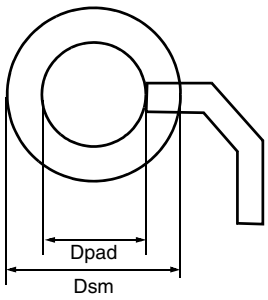
Figure 43. 144-low profile fine pitch ball grid array package



Dim.	mm			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	1.21		1.70	0.0476		0.0669
A1	0.21			0.0083		
A2		1.085			0.0427	
b	0.35	0.40	0.45	0.0138	0.0157	0.0177
D	9.85	10.00	10.15	0.3878	0.3937	0.3996
D1		8.80			0.3465	
E	9.85	10.00	10.15	0.3878	0.3937	0.3996
E1		8.80			0.3465	
e		0.80			0.0315	
F		0.60			0.0236	
ddd			0.10			0.0039
eee			0.15			0.0059
fff			0.08			0.0031
	Number of Pins					
N	144					

[1]Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 44. Recommended PCB design rules (0.80/0.75mm pitch BGA)



Dpad	0.37 mm
Dsm	0.52 mm typ. (depends on solder mask registration tolerance
Solder paste	0.37 mm aperture diameter
– Non solder mask defined pads are recommended – 4 to 6 mils screen print	

5.2 Thermal characteristics

The average chip-junction temperature, T_J, in degrees Celsius, may be calculated using the following equation:

$$T_J = T_A + (P_D \times \Theta_{JA}) \quad (1)$$

Where:

- T_A is the Ambient Temperature in °C,
- Θ_{JA} is the Package Junction-to-Ambient Thermal Resistance, in °C/W,
- P_D is the sum of P_{INT} and $P_{I/O}$ ($P_D = P_{INT} + P_{I/O}$),
- P_{INT} is the product of I_{DD} and V_{DD}, expressed in Watts. This is the Chip Internal Power.

$P_{I/O}$ represents the Power Dissipation on Input and Output Pins;

Most of the time for the application $P_{I/O} < P_{INT}$ and can be neglected. On the other hand, $P_{I/O}$ may be significant if the device is configured to drive continuously external modules and/or memories.

An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is given by:

$$P_D = K / (T_J + 273°C) \quad (2)$$

Therefore (solving equations 1 and 2):

$$K = P_D \times (T_A + 273°C) + \Theta_{JA} \times P_D^2 \quad (3)$$

where:

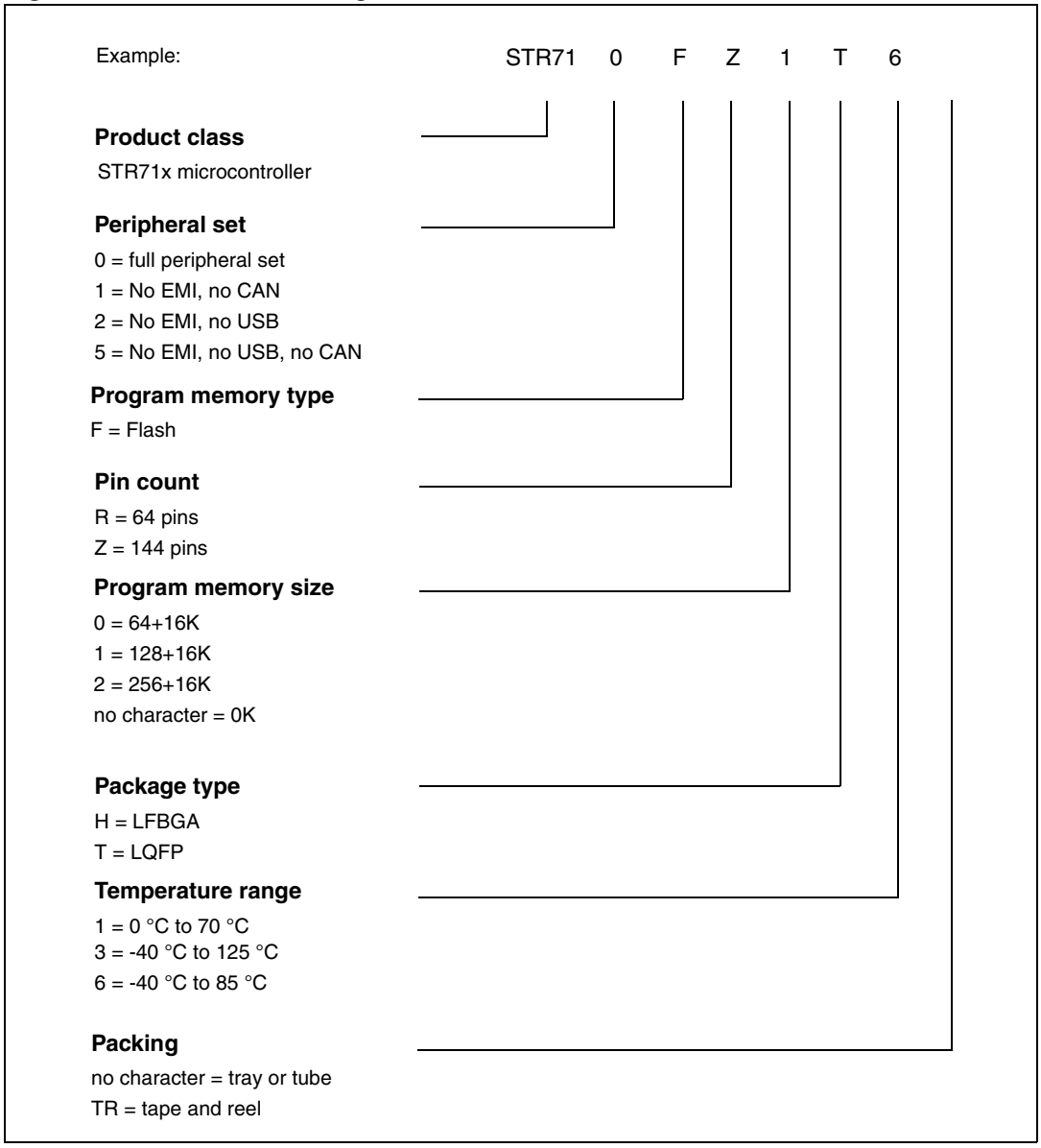
K is a constant for the particular part, which may be determined from equation (3) by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J may be obtained by solving equations (1) and (2) iteratively for any value of T_A.

Table 42. Thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	Thermal Resistance Junction-Ambient LQFP 144 - 20 x 20 mm / 0.5 mm pitch	42	°C/W
Θ_{JA}	Thermal Resistance Junction-Ambient LQFP 64 - 10 x 10 mm / 0.5 mm pitch	45	°C/W
Θ_{JA}	Thermal Resistance Junction-Ambient LFBGA 64 - 8 x 8 x 1.7mm	58	°C/W
Θ_{JA}	Thermal Resistance Junction-Ambient LFBGA 144 - 10 x 10 x 1.7mm	50	°C/W

7 Ordering information

Figure 49. STR71xF ordering information scheme



1. For a list of available options (e.g. memory size, package) and orderable part numbers or for further information on any aspect of this device, please go to www.st.com or contact the ST Sales Office nearest to you.

Table 44. Document revision history (continued)

Date	Revision	Changes
22-May-2006	8	Added Flashless device. Changed reset state of pins P1.10 and P1.13 from pu to pd, P0.15 from pu to floating and removed x in interrupt column for P1.15 and P1.12 in *Table 4* and *Table 5* Added notes under *Table 4* on EMI pin reset state. Corrected inch value for d3 in *Figure 40* Added footprint diagrams in *Figure 40* and *Figure 43* Updated *Section 4: Electrical parameters*
01-Aug-2006	9	Flash data retention changed to 20 years at 85° C. Changed note 8 on page 19 Changed note 1 on page 45
06-Nov-2006	10	Added STR715FR0T1 in *Table 42: Order codes* P0.12 corrected in *Table 5 on page 25*
20-Mar-2007	11	Added characteristics of *BSPI - buffered serial peripheral interface on page 63* Updated *Table 21: Low-power mode wakeup timing on page 46*
13-Feb-2008	12	Updated ordering information Updated USB characteristics Updated external clock characteristics
03-Apr-2013	13	Updated title (to be in line with the “device summary” table) Updated ST Logo and Disclaimer Added *Section 8: Known limitations*